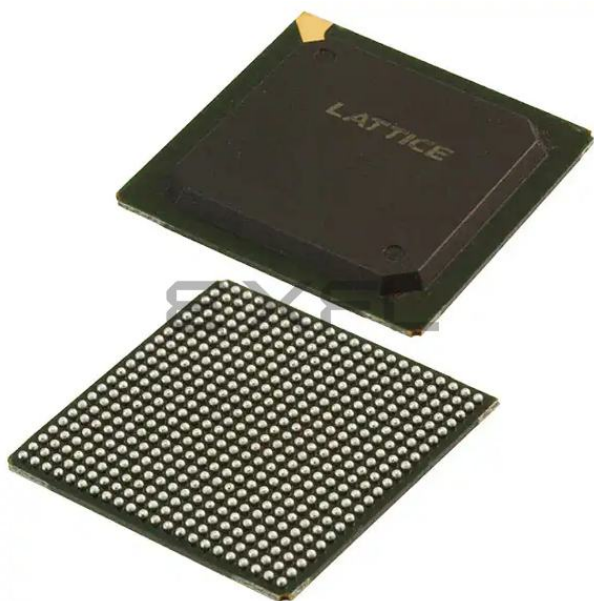




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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	540
Number of Logic Elements/Cells	4320
Total RAM Bits	94208
Number of I/O	278
Number of Gates	-
Voltage - Supply	1.14V ~ 1.26V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	484-BBGA
Supplier Device Package	484-FBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/lattice-semiconductor/lcmxo2-4000ze-1fg484c

Features

■ Flexible Logic Architecture

- Six devices with 256 to 6864 LUT4s and 18 to 334 I/Os

■ Ultra Low Power Devices

- Advanced 65 nm low power process
- As low as 22 μ W standby power
- Programmable low swing differential I/Os
- Stand-by mode and other power saving options

■ Embedded and Distributed Memory

- Up to 240 kbits sysMEM™ Embedded Block RAM
- Up to 54 kbits Distributed RAM
- Dedicated FIFO control logic

■ On-Chip User Flash Memory

- Up to 256 kbits of User Flash Memory
- 100,000 write cycles
- Accessible through WISHBONE, SPI, I²C and JTAG interfaces
- Can be used as soft processor PROM or as Flash memory

■ Pre-Engineered Source Synchronous I/O

- DDR registers in I/O cells
- Dedicated gearing logic
- 7:1 Gearing for Display I/Os
- Generic DDR, DDRX2, DDRX4
- Dedicated DDR/DDR2/LPDDR memory with QDS support

■ High Performance, Flexible I/O Buffer

- Programmable sysIO™ buffer supports wide range of interfaces:
 - LVCMOS 3.3/2.5/1.8/1.5/1.2
 - LVTTTL
 - PCI
 - LVDS, Bus-LVDS, MLVDS, RSDS, LVPECL
 - SSTL 25/18
 - HSTL 18
 - Schmitt trigger inputs, up to 0.5 V hysteresis
- I/Os support hot socketing
- On-chip differential termination
- Programmable pull-up or pull-down mode

■ Flexible On-Chip Clocking

- Eight primary clocks
- Up to two edge clocks for high-speed I/O interfaces (top and bottom sides only)
- Up to two analog PLLs per device with fractional-n frequency synthesis
 - Wide input frequency range (7 MHz to 400 MHz)

■ Non-volatile, Infinitely Reconfigurable

- Instant-on – powers up in microseconds
- Single-chip, secure solution
- Programmable through JTAG, SPI or I²C
- Supports background programming of non-volatile memory
- Optional dual boot with external SPI memory

■ TransFR™ Reconfiguration

- In-field logic update while system operates

■ Enhanced System Level Support

- On-chip hardened functions: SPI, I²C, timer/counter
- On-chip oscillator with 5.5% accuracy
- Unique TraceID for system tracking
- One Time Programmable (OTP) mode
- Single power supply with extended operating range
- IEEE Standard 1149.1 boundary scan
- IEEE 1532 compliant in-system programming

■ Broad Range of Package Options

- TQFP, WLCSP, ucBGA, csBGA, caBGA, ftBGA, fpBGA, QFN package options
- Small footprint package options
 - As small as 2.5 mm x 2.5 mm
- Density migration supported
- Advanced halogen-free packaging

Table 2-4. PLL Signal Descriptions (Continued)

Port Name	I/O	Description
CLKOP	O	Primary PLL output clock (with phase shift adjustment)
CLKOS	O	Secondary PLL output clock (with phase shift adjust)
CLKOS2	O	Secondary PLL output clock2 (with phase shift adjust)
CLKOS3	O	Secondary PLL output clock3 (with phase shift adjust)
LOCK	O	PLL LOCK, asynchronous signal. Active high indicates PLL is locked to input and feedback signals.
DPHSRC	O	Dynamic Phase source – ports or WISHBONE is active
STDBY	I	Standby signal to power down the PLL
RST	I	PLL reset without resetting the M-divider. Active high reset.
RESETM	I	PLL reset - includes resetting the M-divider. Active high reset.
RESETC	I	Reset for CLKOS2 output divider only. Active high reset.
RESETD	I	Reset for CLKOS3 output divider only. Active high reset.
ENCLKOP	I	Enable PLL output CLKOP
ENCLKOS	I	Enable PLL output CLKOS when port is active
ENCLKOS2	I	Enable PLL output CLKOS2 when port is active
ENCLKOS3	I	Enable PLL output CLKOS3 when port is active
PLLCLK	I	PLL data bus clock input signal
PLL_RST	I	PLL data bus reset. This resets only the data bus not any register values.
PLLSTB	I	PLL data bus strobe signal
PLLWE	I	PLL data bus write enable signal
PLLADDR [4:0]	I	PLL data bus address
PLLDAT_I [7:0]	I	PLL data bus data input
PLLDAT_O [7:0]	O	PLL data bus data output
PLLACK	O	PLL data bus acknowledge signal

sysMEM Embedded Block RAM Memory

The MachXO2-640/U and larger devices contain sysMEM Embedded Block RAMs (EBRs). The EBR consists of a 9-kbit RAM, with dedicated input and output registers. This memory can be used for a wide variety of purposes including data buffering, PROM for the soft processor and FIFO.

sysMEM Memory Block

The sysMEM block can implement single port, dual port, pseudo dual port, or FIFO memories. Each block can be used in a variety of depths and widths as shown in Table 2-5.

Figure 2-8. sysMEM Memory Primitives

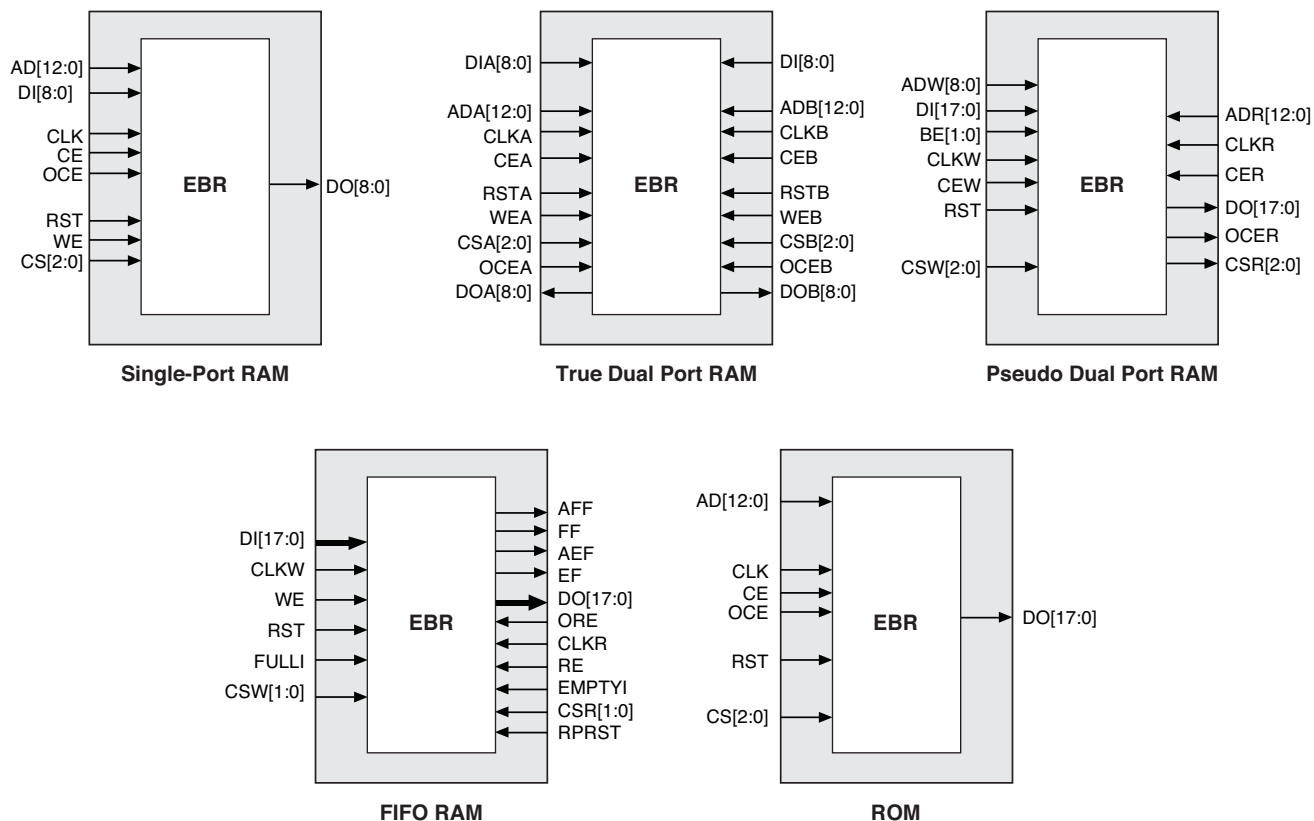


Table 2-6. EBR Signal Descriptions

Port Name	Description	Active State
CLK	Clock	Rising Clock Edge
CE	Clock Enable	Active High
OCE ¹	Output Clock Enable	Active High
RST	Reset	Active High
BE ¹	Byte Enable	Active High
WE	Write Enable	Active High
AD	Address Bus	—
DI	Data In	—
DO	Data Out	—
CS	Chip Select	Active High
AFF	FIFO RAM Almost Full Flag	—
FF	FIFO RAM Full Flag	—
AEF	FIFO RAM Almost Empty Flag	—
EF	FIFO RAM Empty Flag	—
RPRST	FIFO RAM Read Pointer Reset	—

1. Optional signals.
2. For dual port EBR primitives a trailing 'A' or 'B' in the signal name specifies the EBR port A or port B respectively.
3. For FIFO RAM mode primitive, a trailing 'R' or 'W' in the signal name specifies the FIFO read port or write port respectively.
4. For FIFO RAM mode primitive FULLI has the same function as CSW(2) and EMPTYI has the same function as CSR(2).
5. In FIFO mode, CLKW is the write port clock, CSW is the write port chip select, CLKR is the read port clock, CSR is the read port chip select, ORE is the output read enable.

PIO

The PIO contains three blocks: an input register block, output register block and tri-state register block. These blocks contain registers for operating in a variety of modes along with the necessary clock and selection logic.

Table 2-8. PIO Signal List

Pin Name	I/O Type	Description
CE	Input	Clock Enable
D	Input	Pin input from sysIO buffer.
INDD	Output	Register bypassed input.
INCK	Output	Clock input
Q0	Output	DDR positive edge input
Q1	Output	Registered input/DDR negative edge input
D0	Input	Output signal from the core (SDR and DDR)
D1	Input	Output signal from the core (DDR)
TD	Input	Tri-state signal from the core
Q	Output	Data output signals to sysIO Buffer
TQ	Output	Tri-state output signals to sysIO Buffer
DQSR90 ¹	Input	DQS shift 90-degree read clock
DQSW90 ¹	Input	DQS shift 90-degree write clock
DDRCLKPOL ¹	Input	DDR input register polarity control signal from DQS
SCLK	Input	System clock for input and output/tri-state blocks.
RST	Input	Local set reset signal

1. Available in PIO on right edge only.

Input Register Block

The input register blocks for the PIOs on all edges contain delay elements and registers that can be used to condition high-speed interface signals before they are passed to the device core. In addition to this functionality, the input register blocks for the PIOs on the right edge include built-in logic to interface to DDR memory.

Figure 2-12 shows the input register block for the PIOs located on the left, top and bottom edges. Figure 2-13 shows the input register block for the PIOs on the right edge.

Left, Top, Bottom Edges

Input signals are fed from the sysIO buffer to the input register block (as signal D). If desired, the input signal can bypass the register and delay elements and be used directly as a combinatorial signal (INDD), and a clock (INCK). If an input delay is desired, users can select a fixed delay. I/Os on the bottom edge also have a dynamic delay, DEL[4:0]. The delay, if selected, reduces input register hold time requirements when using a global clock. The input block allows two modes of operation. In single data rate (SDR) the data is registered with the system clock (SCLK) by one of the registers in the single data rate sync register block. In Generic DDR mode, two registers are used to sample the data on the positive and negative edges of the system clock (SCLK) signal, creating two data streams.

These gearboxes have three stage pipeline registers. The first stage registers sample the high-speed input data by the high-speed edge clock on its rising and falling edges. The second stage registers perform data alignment based on the control signals UPDATE and SEL0 from the control block. The third stage pipeline registers pass the data to the device core synchronized to the low-speed system clock. Figure 2-16 shows a block diagram of the input gearbox.

Figure 2-16. Input Gearbox

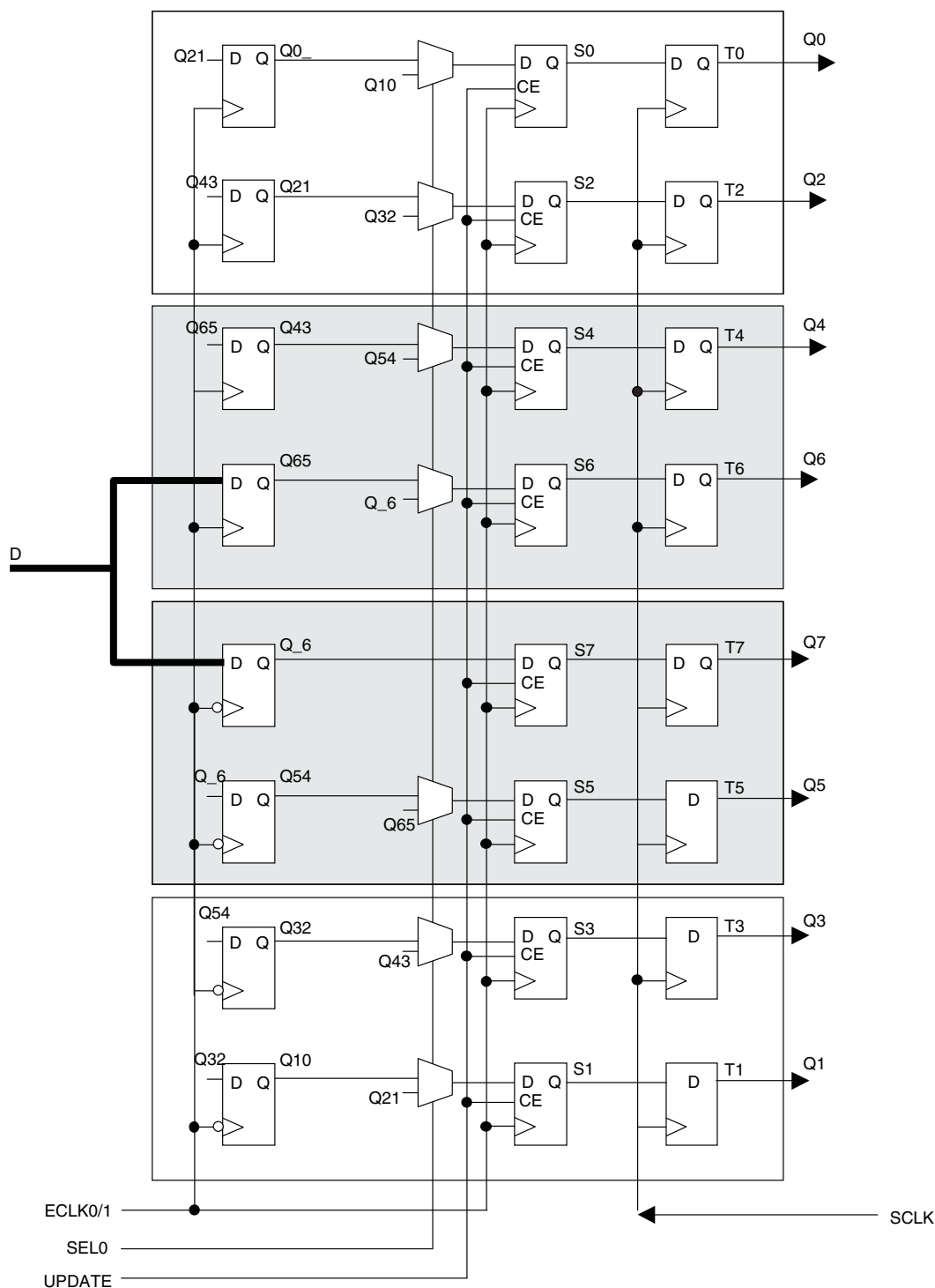


Table 2-13. Supported Output Standards

Output Standard	V _{CCIO} (Typ.)
Single-Ended Interfaces	
LVTTL	3.3
LVC MOS33	3.3
LVC MOS25	2.5
LVC MOS18	1.8
LVC MOS15	1.5
LVC MOS12	1.2
LVC MOS33, Open Drain	—
LVC MOS25, Open Drain	—
LVC MOS18, Open Drain	—
LVC MOS15, Open Drain	—
LVC MOS12, Open Drain	—
PCI33	3.3
SSTL25 (Class I)	2.5
SSTL18 (Class I)	1.8
HSTL18(Class I)	1.8
Differential Interfaces	
LVDS ^{1,2}	2.5, 3.3
BLVDS, MLVDS, RSDS ²	2.5
LVPECL ²	3.3
MIPI ²	2.5
Differential SSTL18	1.8
Differential SSTL25	2.5
Differential HSTL18	1.8

1. MachXO2-640U, MachXO2-1200/U and larger devices have dedicated LVDS buffers.

2. These interfaces can be emulated with external resistors in all devices.

sysIO Buffer Banks

The numbers of banks vary between the devices of this family. MachXO2-1200U, MachXO2-2000/U and higher density devices have six I/O banks (one bank on the top, right and bottom side and three banks on the left side). The MachXO2-1200 and lower density devices have four banks (one bank per side). Figures 2-18 and 2-19 show the sysIO banks and their associated supplies for all devices.

Figure 2-18. MachXO2-1200U, MachXO2-2000/U, MachXO2-4000 and MachXO2-7000 Banks

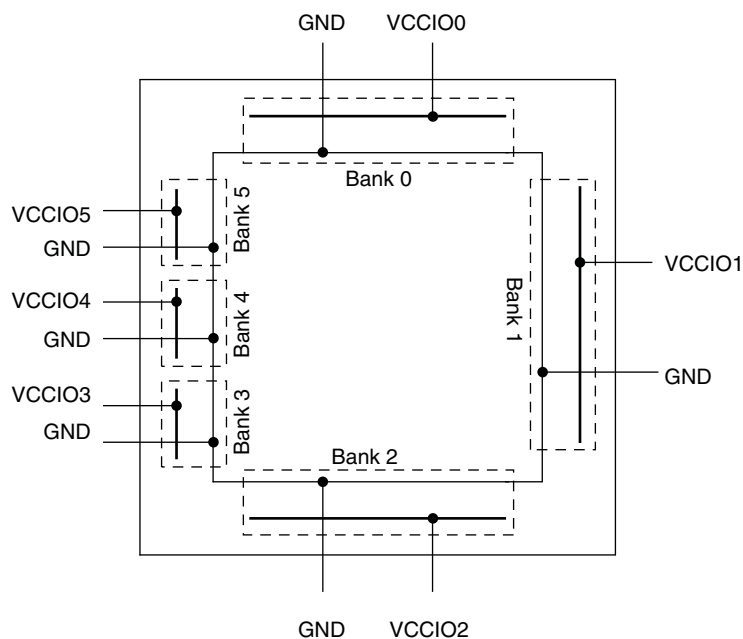
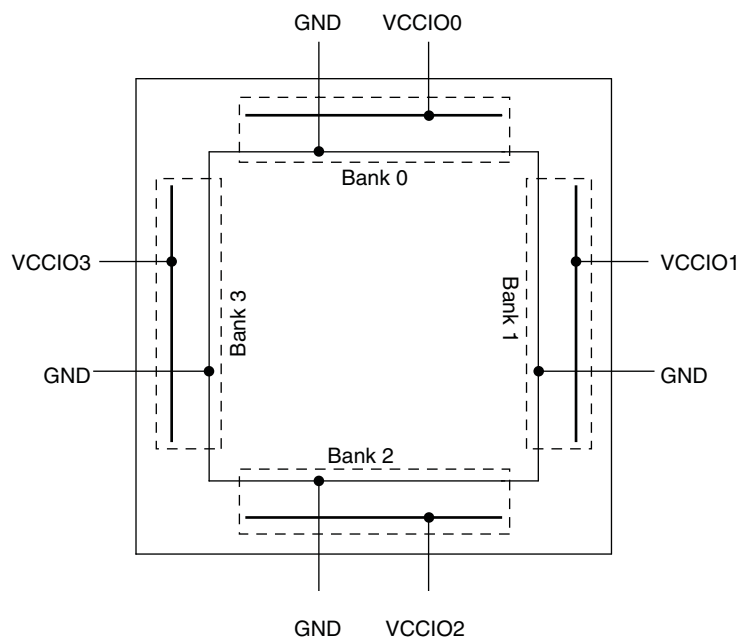


Figure 2-19. MachXO2-256, MachXO2-640/U and MachXO2-1200 Banks



Configuration and Testing

This section describes the configuration and testing features of the MachXO2 family.

IEEE 1149.1-Compliant Boundary Scan Testability

All MachXO2 devices have boundary scan cells that are accessed through an IEEE 1149.1 compliant test access port (TAP). This allows functional testing of the circuit board, on which the device is mounted, through a serial scan path that can access all critical logic nodes. Internal registers are linked internally, allowing test data to be shifted in and loaded directly onto test nodes, or test data to be captured and shifted out for verification. The test access port consists of dedicated I/Os: TDI, TDO, TCK and TMS. The test access port shares its power supply with V_{CCIO} Bank 0 and can operate with LVCMOS3.3, 2.5, 1.8, 1.5, and 1.2 standards.

For more details on boundary scan test, see AN8066, [Boundary Scan Testability with Lattice sysIO Capability](#) and TN1087, [Minimizing System Interruption During Configuration Using TransFR Technology](#).

Device Configuration

All MachXO2 devices contain two ports that can be used for device configuration. The Test Access Port (TAP), which supports bit-wide configuration and the sysCONFIG port which supports serial configuration through I²C or SPI. The TAP supports both the IEEE Standard 1149.1 Boundary Scan specification and the IEEE Standard 1532 In-System Configuration specification. There are various ways to configure a MachXO2 device:

1. Internal Flash Download
2. JTAG
3. Standard Serial Peripheral Interface (Master SPI mode) – interface to boot PROM memory
4. System microprocessor to drive a serial slave SPI port (SSPI mode)
5. Standard I²C Interface to system microprocessor

Upon power-up, the configuration SRAM is ready to be configured using the selected sysCONFIG port. Once a configuration port is selected, it will remain active throughout that configuration cycle. The IEEE 1149.1 port can be activated any time after power-up by sending the appropriate command through the TAP port. Optionally the device can run a CRC check upon entering the user mode. This will ensure that the device was configured correctly.

The sysCONFIG port has 10 dual-function pins which can be used as general purpose I/Os if they are not required for configuration. See TN1204, [MachXO2 Programming and Configuration Usage Guide](#) for more information about using the dual-use pins as general purpose I/Os.

Lattice design software uses proprietary compression technology to compress bit-streams for use in MachXO2 devices. Use of this technology allows Lattice to provide a lower cost solution. In the unlikely event that this technology is unable to compress bitstreams to fit into the amount of on-chip Flash memory, there are a variety of techniques that can be utilized to allow the bitstream to fit in the on-chip Flash memory. For more details, refer to TN1204, [MachXO2 Programming and Configuration Usage Guide](#).

The Test Access Port (TAP) has five dual purpose pins (TDI, TDO, TMS, TCK and JTAGENB). These pins are dual function pins - TDI, TDO, TMS and TCK can be used as general purpose I/O if desired. For more details, refer to TN1204, [MachXO2 Programming and Configuration Usage Guide](#).

TransFR (Transparent Field Reconfiguration)

TransFR is a unique Lattice technology that allows users to update their logic in the field without interrupting system operation using a simple push-button solution. For more details refer to TN1087, [Minimizing System Interruption During Configuration Using TransFR Technology](#) for details.

Power-On-Reset Voltage Levels^{1, 2, 3, 4, 5}

Symbol	Parameter	Min.	Typ.	Max.	Units
V_{PORUP}	Power-On-Reset ramp up trip point (band gap based circuit monitoring V_{CCINT} and V_{CCIO0})	0.9	—	1.06	V
$V_{PORUPEXT}$	Power-On-Reset ramp up trip point (band gap based circuit monitoring external V_{CC} power supply)	1.5	—	2.1	V
$V_{PORDNBG}$	Power-On-Reset ramp down trip point (band gap based circuit monitoring V_{CCINT})	0.75	—	0.93	V
$V_{PORDNBGEXT}$	Power-On-Reset ramp down trip point (band gap based circuit monitoring V_{CC})	0.98	—	1.33	V
$V_{PORDNSRAM}$	Power-On-Reset ramp down trip point (SRAM based circuit monitoring V_{CCINT})	—	0.6	—	V
$V_{PORDNSRAMEXT}$	Power-On-Reset ramp down trip point (SRAM based circuit monitoring V_{CC})	—	0.96	—	V

1. These POR trip points are only provided for guidance. Device operation is only characterized for power supply voltages specified under recommended operating conditions.
2. For devices without voltage regulators V_{CCINT} is the same as the V_{CC} supply voltage. For devices with voltage regulators, V_{CCINT} is regulated from the V_{CC} supply voltage.
3. Note that V_{PORUP} (min.) and $V_{PORDNBG}$ (max.) are in different process corners. For any given process corner $V_{PORDNBG}$ (max.) is always 12.0 mV below V_{PORUP} (min.).
4. $V_{PORUPEXT}$ is for HC devices only. In these devices a separate POR circuit monitors the external V_{CC} power supply.
5. V_{CCIO0} does not have a Power-On-Reset ramp down trip point. V_{CCIO0} must remain within the Recommended Operating Conditions to ensure proper operation.

Programming/Erase Specifications

Symbol	Parameter	Min.	Max. ¹	Units
N_{PROG}	Flash Programming cycles per $t_{RETENTION}$	—	10,000	Cycles
	Flash functional programming cycles	—	100,000	
$t_{RETENTION}$	Data retention at 100 °C junction temperature	10	—	Years
	Data retention at 85 °C junction temperature	20	—	

1. Maximum Flash memory reads are limited to 7.5E13 cycles over the lifetime of the product.

Hot Socketing Specifications^{1, 2, 3}

Symbol	Parameter	Condition	Max.	Units
I_{DK}	Input or I/O leakage Current	$0 < V_{IN} < V_{IH}$ (MAX)	+/-1000	μA

1. Insensitive to sequence of V_{CC} and V_{CCIO} . However, assumes monotonic rise/fall rates for V_{CC} and V_{CCIO} .
2. $0 < V_{CC} < V_{CC} (MAX)$, $0 < V_{CCIO} < V_{CCIO} (MAX)$.
3. I_{DK} is additive to I_{PU} , I_{PD} or I_{BH} .

ESD Performance

Please refer to the [MachXO2 Product Family Qualification Summary](#) for complete qualification data, including ESD performance.

sysIO Recommended Operating Conditions

Standard	V _{CCIO} (V)			V _{REF} (V)		
	Min.	Typ.	Max.	Min.	Typ.	Max.
LVC MOS 3.3	3.135	3.3	3.6	—	—	—
LVC MOS 2.5	2.375	2.5	2.625	—	—	—
LVC MOS 1.8	1.71	1.8	1.89	—	—	—
LVC MOS 1.5	1.425	1.5	1.575	—	—	—
LVC MOS 1.2	1.14	1.2	1.26	—	—	—
LVTTL	3.135	3.3	3.6	—	—	—
PCI ³	3.135	3.3	3.6	—	—	—
SSTL25	2.375	2.5	2.625	1.15	1.25	1.35
SSTL18	1.71	1.8	1.89	0.833	0.9	0.969
HSTL18	1.71	1.8	1.89	0.816	0.9	1.08
LVC MOS25R33	3.135	3.3	3.6	1.1	1.25	1.4
LVC MOS18R33	3.135	3.3	3.6	0.75	0.9	1.05
LVC MOS18R25	2.375	2.5	2.625	0.75	0.9	1.05
LVC MOS15R33	3.135	3.3	3.6	0.6	0.75	0.9
LVC MOS15R25	2.375	2.5	2.625	0.6	0.75	0.9
LVC MOS12R33 ⁴	3.135	3.3	3.6	0.45	0.6	0.75
LVC MOS12R25 ⁴	2.375	2.5	2.625	0.45	0.6	0.75
LVC MOS10R33 ⁴	3.135	3.3	3.6	0.35	0.5	0.65
LVC MOS10R25 ⁴	2.375	2.5	2.625	0.35	0.5	0.65
LVDS25 ^{1, 2}	2.375	2.5	2.625	—	—	—
LVDS33 ^{1, 2}	3.135	3.3	3.6	—	—	—
LVPECL ¹	3.135	3.3	3.6	—	—	—
BLVDS ¹	2.375	2.5	2.625	—	—	—
RSDS ¹	2.375	2.5	2.625	—	—	—
SSTL18D	1.71	1.8	1.89	—	—	—
SSTL25D	2.375	2.5	2.625	—	—	—
HSTL18D	1.71	1.8	1.89	—	—	—

1. Inputs on-chip. Outputs are implemented with the addition of external resistors.

2. MachXO2-640U, MachXO2-1200/U and larger devices have dedicated LVDS buffers.

3. Input on the bottom bank of the MachXO2-640U, MachXO2-1200/U and larger devices only.

4. Supported only for inputs and BIDs for all ZE devices, and –6 speed grade for HE and HC devices.

sysIO Single-Ended DC Electrical Characteristics^{1, 2}

Input/Output Standard	V_{IL}		V_{IH}		V_{OL} Max. (V)	V_{OH} Min. (V)	I_{OL} Max. ⁴ (mA)	I_{OH} Max. ⁴ (mA)
	Min. (V) ³	Max. (V)	Min. (V)	Max. (V)				
LVCMOS 3.3 LVTTL	-0.3	0.8	2.0	3.6	0.4	$V_{CCIO} - 0.4$	4	-4
							8	-8
							12	-12
							16	-16
							24	-24
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVCMOS 2.5	-0.3	0.7	1.7	3.6	0.4	$V_{CCIO} - 0.4$	4	-4
							8	-8
							12	-12
							16	-16
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVCMOS 1.8	-0.3	$0.35V_{CCIO}$	$0.65V_{CCIO}$	3.6	0.4	$V_{CCIO} - 0.4$	4	-4
							8	-8
							12	-12
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVCMOS 1.5	-0.3	$0.35V_{CCIO}$	$0.65V_{CCIO}$	3.6	0.4	$V_{CCIO} - 0.4$	4	-4
							8	-8
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
LVCMOS 1.2	-0.3	$0.35V_{CCIO}$	$0.65V_{CCIO}$	3.6	0.4	$V_{CCIO} - 0.4$	4	-2
							8	-6
					0.2	$V_{CCIO} - 0.2$	0.1	-0.1
PCI	-0.3	$0.3V_{CCIO}$	$0.5V_{CCIO}$	3.6	$0.1V_{CCIO}$	$0.9V_{CCIO}$	1.5	-0.5
SSTL25 Class I	-0.3	$V_{REF} - 0.18$	$V_{REF} + 0.18$	3.6	0.54	$V_{CCIO} - 0.62$	8	8
SSTL25 Class II	-0.3	$V_{REF} - 0.18$	$V_{REF} + 0.18$	3.6	NA	NA	NA	NA
SSTL18 Class I	-0.3	$V_{REF} - 0.125$	$V_{REF} + 0.125$	3.6	0.40	$V_{CCIO} - 0.40$	8	8
SSTL18 Class II	-0.3	$V_{REF} - 0.125$	$V_{REF} + 0.125$	3.6	NA	NA	NA	NA
HSTL18 Class I	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	0.40	$V_{CCIO} - 0.40$	8	8
HSTL18 Class II	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	NA	NA	NA	NA
LVCMOS25R33	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	NA	NA	NA	NA
LVCMOS18R33	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	NA	NA	NA	NA
LVCMOS18R25	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	NA	NA	NA	NA
LVCMOS15R33	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	NA	NA	NA	NA
LVCMOS15R25	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	NA	NA	NA	NA
LVCMOS12R33	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	0.40	NA Open Drain	24, 16, 12, 8, 4	NA Open Drain
LVCMOS12R25	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	0.40	NA Open Drain	16, 12, 8, 4	NA Open Drain
LVCMOS10R33	-0.3	$V_{REF} - 0.1$	$V_{REF} + 0.1$	3.6	0.40	NA Open Drain	24, 16, 12, 8, 4	NA Open Drain

LVDS Emulation

MachXO2 devices can support LVDS outputs via emulation (LVDS25E). The output is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs on all devices. The scheme shown in Figure 3-1 is one possible solution for LVDS standard implementation. Resistor values in Figure 3-1 are industry standard values for 1% resistors.

Figure 3-1. LVDS Using External Resistors (LVDS25E)

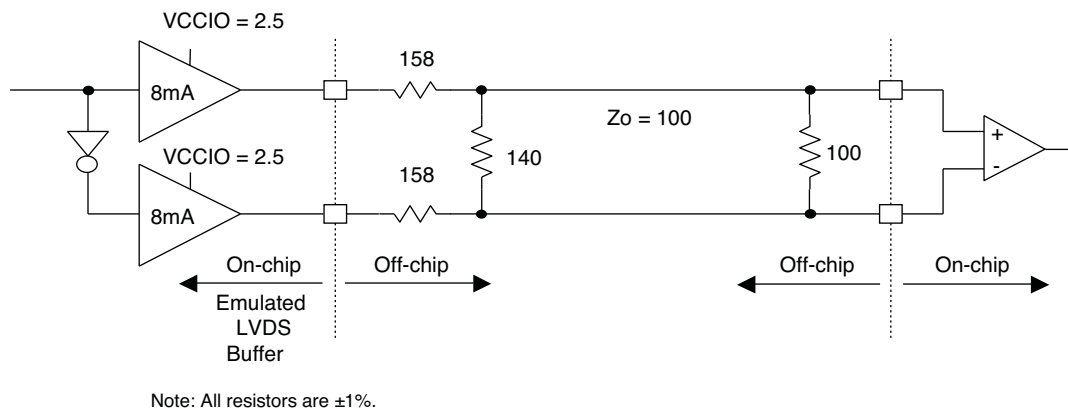


Table 3-1. LVDS25E DC Conditions

Over Recommended Operating Conditions

Parameter	Description	Typ.	Units
Z_{OUT}	Output impedance	20	Ohms
R_S	Driver series resistor	158	Ohms
R_P	Driver parallel resistor	140	Ohms
R_T	Receiver termination	100	Ohms
V_{OH}	Output high voltage	1.43	V
V_{OL}	Output low voltage	1.07	V
V_{OD}	Output differential voltage	0.35	V
V_{CM}	Output common mode voltage	1.25	V
Z_{BACK}	Back impedance	100.5	Ohms
I_{DC}	DC output current	6.03	mA

BLVDS

The MachXO2 family supports the BLVDS standard through emulation. The output is emulated using complementary LVCMOS outputs in conjunction with resistors across the driver outputs. The input standard is supported by the LVDS differential input buffer. BLVDS is intended for use when multi-drop and bi-directional multi-point differential signaling is required. The scheme shown in Figure 3-2 is one possible solution for bi-directional multi-point differential signals.

Figure 3-2. BLVDS Multi-point Output Example

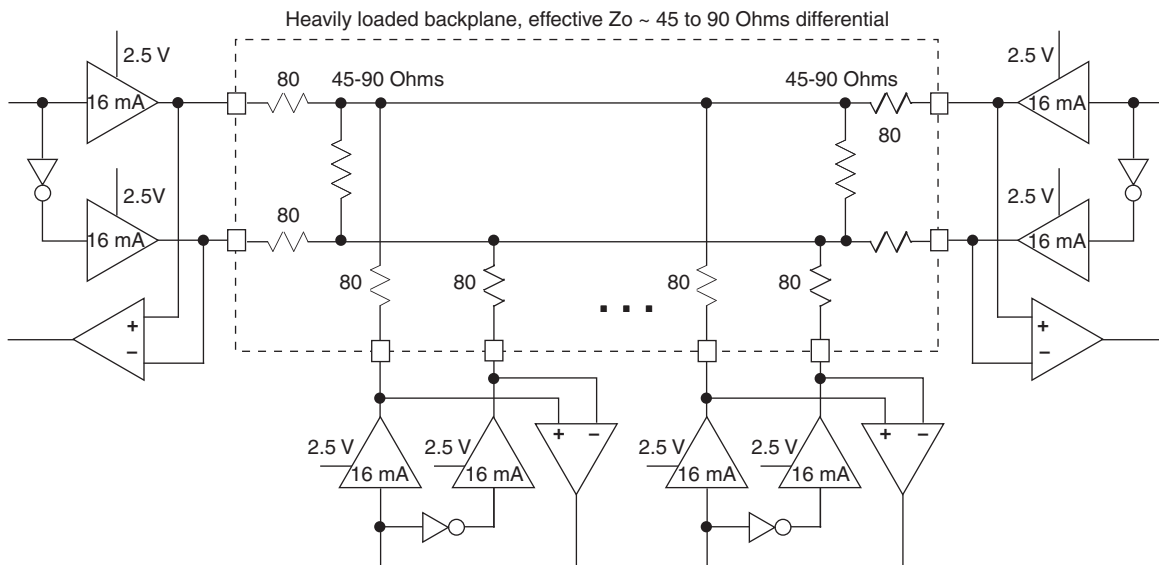


Table 3-2. BLVDS DC Conditions¹

Over Recommended Operating Conditions

Symbol	Description	Nominal		Units
		Zo = 45	Zo = 90	
Z _{OUT}	Output impedance	20	20	Ohms
R _S	Driver series resistance	80	80	Ohms
R _{TLEFT}	Left end termination	45	90	Ohms
R _{TRIGHT}	Right end termination	45	90	Ohms
V _{OH}	Output high voltage	1.376	1.480	V
V _{OL}	Output low voltage	1.124	1.020	V
V _{OD}	Output differential voltage	0.253	0.459	V
V _{CM}	Output common mode voltage	1.250	1.250	V
I _{DC}	DC output current	11.236	10.204	mA

1. For input buffer, see LVDS table.

Parameter	Description	Device	-6		-5		-4		Units
			Min.	Max.	Min.	Max.	Min.	Max.	
LPDDR ^{9, 12}									
t _{DVADQ}	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only. ¹³	—	0.369	—	0.395	—	0.421	UI
t _{DVEDQ}	Input Data Hold After DQS Input		0.529	—	0.530	—	0.527	—	UI
t _{DQVBS}	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t _{DQVAS}	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f _{DATA}	MEM LPDDR Serial Data Speed		—	280	—	250	—	208	Mbps
f _{SCLK}	SCLK Frequency		—	140	—	125	—	104	MHz
f _{LPDDR}	LPDDR Data Transfer Rate		0	280	0	250	0	208	Mbps
DDR ^{9, 12}									
t _{DVADQ}	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only. ¹³	—	0.350	—	0.387	—	0.414	UI
t _{DVEDQ}	Input Data Hold After DQS Input		0.545	—	0.538	—	0.532	—	UI
t _{DQVBS}	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t _{DQVAS}	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f _{DATA}	MEM DDR Serial Data Speed		—	300	—	250	—	208	Mbps
f _{SCLK}	SCLK Frequency		—	150	—	125	—	104	MHz
f _{MEM_DDR}	MEM DDR Data Transfer Rate		N/A	300	N/A	250	N/A	208	Mbps
DDR2 ^{9, 12}									
t _{DVADQ}	Input Data Valid After DQS Input	MachXO2-1200/U and larger devices, right side only. ¹³	—	0.360	—	0.378	—	0.406	UI
t _{DVEDQ}	Input Data Hold After DQS Input		0.555	—	0.549	—	0.542	—	UI
t _{DQVBS}	Output Data Invalid Before DQS Output		0.25	—	0.25	—	0.25	—	UI
t _{DQVAS}	Output Data Invalid After DQS Output		0.25	—	0.25	—	0.25	—	UI
f _{DATA}	MEM DDR Serial Data Speed		—	300	—	250	—	208	Mbps
f _{SCLK}	SCLK Frequency		—	150	—	125	—	104	MHz
f _{MEM_DDR2}	MEM DDR2 Data Transfer Rate		N/A	300	N/A	250	N/A	208	Mbps

- Exact performance may vary with device and design implementation. Commercial timing numbers are shown at 85 °C and 1.14 V. Other operating conditions, including industrial, can be extracted from the Diamond software.
- General I/O timing numbers based on LVCMOS 2.5, 8 mA, 0pf load, fast slew rate.
- Generic DDR timing numbers based on LVDS I/O (for input, output, and clock ports).
- DDR timing numbers based on SSTL25. DDR2 timing numbers based on SSTL18. LPDDR timing numbers based in LVCMOS18.
- 7:1 LVDS (GDDR71) uses the LVDS I/O standard (for input, output, and clock ports).
- For Generic DDRX1 mode $t_{SU} = t_{HO} = (t_{DVE} - t_{DVA} - 0.03 \text{ ns})/2$.
- The t_{SU_DEL} and t_{H_DEL} values use the SCLK_ZERHOLD default step size. Each step is 105 ps (-6), 113 ps (-5), 120 ps (-4).
- This number for general purpose usage. Duty cycle tolerance is +/- 10%.
- Duty cycle is +/-5% for system usage.
- The above timing numbers are generated using the Diamond design tool. Exact performance may vary with the device selected.
- High-speed DDR and LVDS not supported in SG32 (32 QFN) packages.
- Advance information for MachXO2 devices in 48 QFN packages.
- DDR memory interface not supported in QN84 (84 QFN) and SG32 (32 QFN) packages.

sysCONFIG Port Timing Specifications

Symbol	Parameter		Min.	Max.	Units
All Configuration Modes					
t _{PRGM}	PROGRAMN low pulse accept		55	—	ns
t _{PRGMJ}	PROGRAMN low pulse rejection		—	25	ns
t _{INITL}	INITN low time	LCMXO2-256	—	30	μs
		LCMXO2-640	—	35	μs
		LCMXO2-640U/ LCMXO2-1200	—	55	μs
		LCMXO2-1200U/ LCMXO2-2000	—	70	μs
		LCMXO2-2000U/ LCMXO2-4000	—	105	μs
		LCMXO2-7000	—	130	μs
t _{DPPINIT}	PROGRAMN low to INITN low		—	150	ns
t _{DPPDONE}	PROGRAMN low to DONE low		—	150	ns
t _{IODISS}	PROGRAMN low to I/O disable		—	120	ns
Slave SPI					
f _{MAX}	CCLK clock frequency		—	66	MHz
t _{CCLKH}	CCLK clock pulse width high		7.5	—	ns
t _{CCLKL}	CCLK clock pulse width low		7.5	—	ns
t _{STSU}	CCLK setup time		2	—	ns
t _{STH}	CCLK hold time		0	—	ns
t _{STCO}	CCLK falling edge to valid output		—	10	ns
t _{STOZ}	CCLK falling edge to valid disable		—	10	ns
t _{STOV}	CCLK falling edge to valid enable		—	10	ns
t _{SCS}	Chip select high time		25	—	ns
t _{SCSS}	Chip select setup time		3	—	ns
t _{SCSH}	Chip select hold time		3	—	ns
Master SPI					
f _{MAX}	MCLK clock frequency		—	133	MHz
t _{MCLKH}	MCLK clock pulse width high		3.75	—	ns
t _{MCLKL}	MCLK clock pulse width low		3.75	—	ns
t _{STSU}	MCLK setup time		5	—	ns
t _{STH}	MCLK hold time		1	—	ns
t _{CSSPI}	INITN high to chip select low		100	200	ns
t _{MCLK}	INITN high to first MCLK edge		0.75	1	μs

For Further Information

For further information regarding logic signal connections for various packages please refer to the MachXO2 Device Pinout Files.

Thermal Management

Thermal management is recommended as part of any sound FPGA design methodology. To assess the thermal characteristics of a system, Lattice specifies a maximum allowable junction temperature in all device data sheets. Users must complete a thermal analysis of their specific design to ensure that the device and package do not exceed the junction temperature limits. Refer to the Thermal Management document to find the device/package specific thermal values.

For Further Information

For further information regarding Thermal Management, refer to the following:

- [Thermal Management](#) document
- TN1198, [Power Estimation and Management for MachXO2 Devices](#)
- The Power Calculator tool is included with the Lattice design tools, or as a standalone download from www.latticesemi.com/software

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-2000ZE-1UWG49ITR ¹	2112	1.2 V	–1	Halogen-Free WLCSP	49	IND
LCMXO2-2000ZE-1UWG49ITR50 ³	2112	1.2 V	–1	Halogen-Free WLCSP	49	IND
LCMXO2-2000ZE-1UWG49ITR1K ²	2112	1.2 V	–1	Halogen-Free WLCSP	49	IND
LCMXO2-2000ZE-1TG100I	2112	1.2 V	–1	Halogen-Free TQFP	100	IND
LCMXO2-2000ZE-2TG100I	2112	1.2 V	–2	Halogen-Free TQFP	100	IND
LCMXO2-2000ZE-3TG100I	2112	1.2 V	–3	Halogen-Free TQFP	100	IND
LCMXO2-2000ZE-1MG132I	2112	1.2 V	–1	Halogen-Free csBGA	132	IND
LCMXO2-2000ZE-2MG132I	2112	1.2 V	–2	Halogen-Free csBGA	132	IND
LCMXO2-2000ZE-3MG132I	2112	1.2 V	–3	Halogen-Free csBGA	132	IND
LCMXO2-2000ZE-1TG144I	2112	1.2 V	–1	Halogen-Free TQFP	144	IND
LCMXO2-2000ZE-2TG144I	2112	1.2 V	–2	Halogen-Free TQFP	144	IND
LCMXO2-2000ZE-3TG144I	2112	1.2 V	–3	Halogen-Free TQFP	144	IND
LCMXO2-2000ZE-1BG256I	2112	1.2 V	–1	Halogen-Free caBGA	256	IND
LCMXO2-2000ZE-2BG256I	2112	1.2 V	–2	Halogen-Free caBGA	256	IND
LCMXO2-2000ZE-3BG256I	2112	1.2 V	–3	Halogen-Free caBGA	256	IND
LCMXO2-2000ZE-1FTG256I	2112	1.2 V	–1	Halogen-Free ftBGA	256	IND
LCMXO2-2000ZE-2FTG256I	2112	1.2 V	–2	Halogen-Free ftBGA	256	IND
LCMXO2-2000ZE-3FTG256I	2112	1.2 V	–3	Halogen-Free ftBGA	256	IND

1. This part number has a tape and reel quantity of 5,000 units with a minimum order quantity of 10,000 units. Order quantities must be in increments of 5,000 units. For example, a 10,000 unit order will be shipped in two reels with one reel containing 5,000 units and the other reel with less than 5,000 units (depending on test yields). Unserviced backlog will be canceled.
2. This part number has a tape and reel quantity of 1,000 units with a minimum order quantity of 1,000. Order quantities must be in increments of 1,000 units. For example, a 5,000 unit order will be shipped as 5 reels of 1000 units each.
3. This part number has a tape and reel quantity of 50 units with a minimum order quantity of 50. Order quantities must be in increments of 50 units. For example, a 1,000 unit order will be shipped as 20 reels of 50 units each.

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-1200ZE-1TG100IR1 ¹	1280	1.2 V	–1	Halogen-Free TQFP	100	IND
LCMXO2-1200ZE-2TG100IR1 ¹	1280	1.2 V	–2	Halogen-Free TQFP	100	IND
LCMXO2-1200ZE-3TG100IR1 ¹	1280	1.2 V	–3	Halogen-Free TQFP	100	IND
LCMXO2-1200ZE-1MG132IR1 ¹	1280	1.2 V	–1	Halogen-Free csBGA	132	IND
LCMXO2-1200ZE-2MG132IR1 ¹	1280	1.2 V	–2	Halogen-Free csBGA	132	IND
LCMXO2-1200ZE-3MG132IR1 ¹	1280	1.2 V	–3	Halogen-Free csBGA	132	IND
LCMXO2-1200ZE-1TG144IR1 ¹	1280	1.2 V	–1	Halogen-Free TQFP	144	IND
LCMXO2-1200ZE-2TG144IR1 ¹	1280	1.2 V	–2	Halogen-Free TQFP	144	IND
LCMXO2-1200ZE-3TG144IR1 ¹	1280	1.2 V	–3	Halogen-Free TQFP	144	IND

1. Specifications for the “LCMXO2-1200ZE-speed package IR1” are the same as the “LCMXO2-1200ZE-speed package I” devices respectively, except as specified in the [R1 Device Specifications](#) section of this data sheet.

High Performance Industrial Grade Devices Without Voltage Regulator, Halogen Free (RoHS) Packaging

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-2000HE-4TG100I	2112	1.2 V	–4	Halogen-Free TQFP	100	IND
LCMXO2-2000HE-5TG100I	2112	1.2 V	–5	Halogen-Free TQFP	100	IND
LCMXO2-2000HE-6TG100I	2112	1.2 V	–6	Halogen-Free TQFP	100	IND
LCMXO2-2000HE-4MG132I	2112	1.2 V	–4	Halogen-Free csBGA	132	IND
LCMXO2-2000HE-5MG132I	2112	1.2 V	–5	Halogen-Free csBGA	132	IND
LCMXO2-2000HE-6MG132I	2112	1.2 V	–6	Halogen-Free csBGA	132	IND
LCMXO2-2000HE-4TG144I	2112	1.2 V	–4	Halogen-Free TQFP	144	IND
LCMXO2-2000HE-5TG144I	2112	1.2 V	–5	Halogen-Free TQFP	144	IND
LCMXO2-2000HE-6TG144I	2112	1.2 V	–6	Halogen-Free TQFP	144	IND
LCMXO2-2000HE-4BG256I	2112	1.2 V	–4	Halogen-Free caBGA	256	IND
LCMXO2-2000HE-5BG256I	2112	1.2 V	–5	Halogen-Free caBGA	256	IND
LCMXO2-2000HE-6BG256I	2112	1.2 V	–6	Halogen-Free caBGA	256	IND
LCMXO2-2000HE-4FTG256I	2112	1.2 V	–4	Halogen-Free ftBGA	256	IND
LCMXO2-2000HE-5FTG256I	2112	1.2 V	–5	Halogen-Free ftBGA	256	IND
LCMXO2-2000HE-6FTG256I	2112	1.2 V	–6	Halogen-Free ftBGA	256	IND

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-2000UHE-4FG484I	2112	1.2 V	–4	Halogen-Free fpBGA	484	IND
LCMXO2-2000UHE-5FG484I	2112	1.2 V	–5	Halogen-Free fpBGA	484	IND
LCMXO2-2000UHE-6FG484I	2112	1.2 V	–6	Halogen-Free fpBGA	484	IND

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-4000HE-4MG132I	4320	1.2 V	–4	Halogen-Free csBGA	132	IND
LCMXO2-4000HE-5MG132I	4320	1.2 V	–5	Halogen-Free csBGA	132	IND
LCMXO2-4000HE-6MG132I	4320	1.2 V	–6	Halogen-Free csBGA	132	IND
LCMXO2-4000HE-4TG144I	4320	1.2 V	–4	Halogen-Free TQFP	144	IND
LCMXO2-4000HE-5TG144I	4320	1.2 V	–5	Halogen-Free TQFP	144	IND
LCMXO2-4000HE-6TG144I	4320	1.2 V	–6	Halogen-Free TQFP	144	IND
LCMXO2-4000HE-4MG184I	4320	1.2 V	–4	Halogen-Free csBGA	184	IND
LCMXO2-4000HE-5MG184I	4320	1.2 V	–5	Halogen-Free csBGA	184	IND
LCMXO2-4000HE-6MG184I	4320	1.2 V	–6	Halogen-Free csBGA	184	IND
LCMXO2-4000HE-4BG256I	4320	1.2 V	–4	Halogen-Free caBGA	256	IND
LCMXO2-4000HE-5BG256I	4320	1.2 V	–5	Halogen-Free caBGA	256	IND
LCMXO2-4000HE-6BG256I	4320	1.2 V	–6	Halogen-Free caBGA	256	IND
LCMXO2-4000HE-4FTG256I	4320	1.2 V	–4	Halogen-Free ftBGA	256	IND
LCMXO2-4000HE-5FTG256I	4320	1.2 V	–5	Halogen-Free ftBGA	256	IND
LCMXO2-4000HE-6FTG256I	4320	1.2 V	–6	Halogen-Free ftBGA	256	IND
LCMXO2-4000HE-4BG332I	4320	1.2 V	–4	Halogen-Free caBGA	332	IND
LCMXO2-4000HE-5BG332I	4320	1.2 V	–5	Halogen-Free caBGA	332	IND
LCMXO2-4000HE-6BG332I	4320	1.2 V	–6	Halogen-Free caBGA	332	IND
LCMXO2-4000HE-4FG484I	4320	1.2 V	–4	Halogen-Free fpBGA	484	IND
LCMXO2-4000HE-5FG484I	4320	1.2 V	–5	Halogen-Free fpBGA	484	IND
LCMXO2-4000HE-6FG484I	4320	1.2 V	–6	Halogen-Free fpBGA	484	IND

Part Number	LUTs	Supply Voltage	Grade	Package	Leads	Temp.
LCMXO2-7000HE-4TG144I	6864	1.2 V	–4	Halogen-Free TQFP	144	IND
LCMXO2-7000HE-5TG144I	6864	1.2 V	–5	Halogen-Free TQFP	144	IND
LCMXO2-7000HE-6TG144I	6864	1.2 V	–6	Halogen-Free TQFP	144	IND
LCMXO2-7000HE-4BG256I	6864	1.2 V	–4	Halogen-Free caBGA	256	IND
LCMXO2-7000HE-5BG256I	6864	1.2 V	–5	Halogen-Free caBGA	256	IND
LCMXO2-7000HE-6BG256I	6864	1.2 V	–6	Halogen-Free caBGA	256	IND
LCMXO2-7000HE-4FTG256I	6864	1.2 V	–4	Halogen-Free ftBGA	256	IND
LCMXO2-7000HE-5FTG256I	6864	1.2 V	–5	Halogen-Free ftBGA	256	IND
LCMXO2-7000HE-6FTG256I	6864	1.2 V	–6	Halogen-Free ftBGA	256	IND
LCMXO2-7000HE-4BG332I	6864	1.2 V	–4	Halogen-Free caBGA	332	IND
LCMXO2-7000HE-5BG332I	6864	1.2 V	–5	Halogen-Free caBGA	332	IND
LCMXO2-7000HE-6BG332I	6864	1.2 V	–6	Halogen-Free caBGA	332	IND
LCMXO2-7000HE-4FG484I	6864	1.2 V	–4	Halogen-Free fpBGA	484	IND
LCMXO2-7000HE-5FG484I	6864	1.2 V	–5	Halogen-Free fpBGA	484	IND
LCMXO2-7000HE-6FG484I	6864	1.2 V	–6	Halogen-Free fpBGA	484	IND